
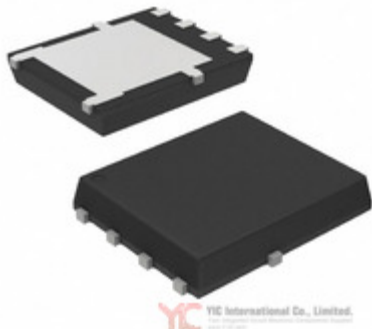
	<h2 style="color: #FF4500;">NVMFS5826NLWFT1G</h2>
	<p>Hersteller-Teilenummer: NVMFS5826NLWFT1G</p> <hr/> <p>Hersteller / Marke: AMI Semiconductor / ON Semiconductor</p> <hr/> <p>Teil der Beschreibung: MOSFET N-CH 60V 26A SO8FL</p> <hr/> <p>Datenblätter:  NVMFS5826NLWFT1G.pdf</p> <hr/> <p>RoHs Status: Bleifrei / RoHS-konform</p> <hr/> <p>Lagerzustand: New original, Stock Available.</p> <hr/> <p>Liefern von: Hong Kong</p> <hr/> <p>Versandweg: DHL/Fedex/TNT/UPS/EMS</p>
	
<p>Image may be representation. See specs for product details.</p>	

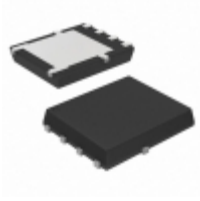
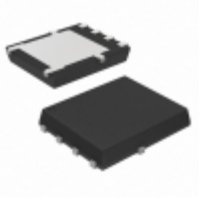
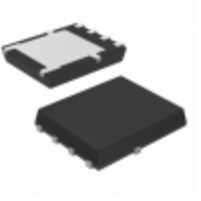
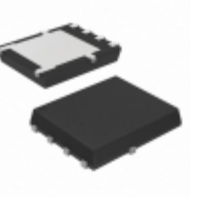
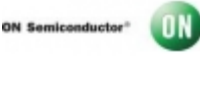
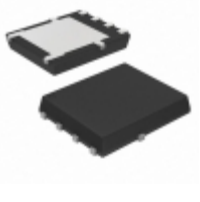
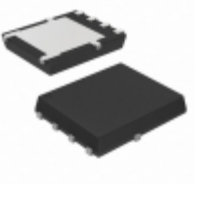
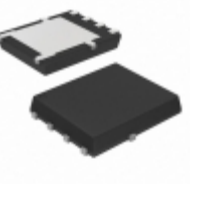
Spezifikationen

Teilenummer	NVMFS5826NLWFT1G
Hersteller	AMI Semiconductor / ON Semiconductor
Beschreibung	MOSFET N-CH 60V 26A SO8FL
Kategorie	Diskrete Halbleiterprodukte > Transistoren-FETs,
Teilstatus	Require For Quote & Check Stock
VGS (th) (Max) @ Id	2.5V @ 250µA
Technologie	MOSFET (Metal Oxide)
Supplier Device-Gehäuse	5-DFN (5x6) (8-SOFL)
Serie	-
Rds On (Max) @ Id, Vgs	24 mOhm @ 10A, 10V
Verlustleistung (max)	3.6W (Ta), 39W (Tc)
Verpackung	Tape & Reel (TR)
Verpackung / Gehäuse	8-PowerTDFN
Betriebstemperatur	-55°C ~ 175°C (TJ)
Befestigungsart	Surface Mount
Eingabekapazität (Ciss) (Max) @ Vds	850pF @ 25V
Gate Charge (Qg) (Max) @ Vgs	17nC @ 10V
Typ FET	N-Channel
FET-Merkmal	-
Drain-Source-Spannung (Vdss)	60V
Strom - Ununterbrochener Abfluss (Id) bei 25 ° C	8A (Ta)

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RFQ NVMFS5826NLWFT1G E-Mail: Info@Y-IC.com

Sie können auch interessiert

<p>sein:</p>  <p>NVMFS5826NLT1G ON Semiconductor MOSFET N-CH 60V 26A SO8FL</p>	 <p>NVMFS5830NLWFT1G ON Semiconductor MOSFET N-CH 40V 172A SO8FL</p>	 <p>NVMFS5830NLWFT3G ON Semiconductor MOSFET N-CH 40V 172A SO8FL</p>	 <p>NVMFS5830NLT1G ON Semiconductor MOSFET N-CH 40V 185A SO8FL</p>
 <p>NVMFS4C310NWFT3G AMI Semiconductor / ON Semiconductor MOSFET N-CH 30V TRENCH</p>	 <p>NVMFS5826NLT3G ON Semiconductor MOSFET N-CH 60V 26A SO8FL</p>	 <p>NVMFS5113PLWFT1G AMI Semiconductor / ON Semiconductor NFET SO8FL 60V 69A 16MOHM</p>	 <p>NVMFS5830NLT3G ON Semiconductor MOSFET N-CH 40V 185A SO8FL</p>

Verwandtes Hot-Keyword

Mehr

NVMFS5826NLWFT1G AMI Semiconductor / ON Semiconductor	NVMFS5826NLWFT1G Datenblatt	NVMFS5826NLWFT1G-Datenblätter	NVMFS5826NLWFT1G PDF	AMI Semiconductor / ON Semiconductor NVMFS5826NLWFT1G
NVMFS5826NLWFT1G Electronic	NVMFS5826NLWFT1G-Komponenten	NVMFS5826NLWFT1G-Verteiler	NVMFS5826NLWFT1G-Bild	NVMFS5826NLWFT1G-Teil
NVMFS5826NLWFT1G Preis	NVMFS5826NLWFT1G Hersteller	NVMFS5826NLWFT1G Bild	NVMFS5826NLWFT1G Aktie	NVMFS5826NLWFT1G Inventar
NVMFS5826NLWFT1G Neu	NVMFS5826NLWFT1G Original	NVMFS5826NLWFT1G garantiert	NVMFS5826NLWFT1G RFQ	NVMFS5826NLWFT1G Online bestellen

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